

Karol Frohlich

List of Publications by Year in descending order

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166
papers

1,982
citations

257357

24
h-index

377752

34
g-index

166
all docs

166
docs citations

166
times ranked

2058
citing authors

#	ARTICLE	IF	CITATIONS
1	Gate insulation and drain current saturation mechanism in InAlN/GaN metal-oxide-semiconductor high-electron-mobility transistors. Applied Physics Letters, 2007, 91, .	1.5	71
2	Effect of crystallinity on the magnetoresistive properties of La _{0.8} MnO ₃ thin films grown by chemical vapor deposition. Applied Physics Letters, 1998, 73, 999-1001.	1.5	57
3	Ultrathin InAlN/AlN Barrier HEMT With High Performance in Normally Off Operation. IEEE Electron Device Letters, 2009, 30, 1030-1032.	2.2	57
4	3D resistive RAM cell design for high-density storage class memory—a review. Science China Information Sciences, 2016, 59, 1.	2.7	54
5	Ru and RuO ₂ gate electrodes for advanced CMOS technology. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2004, 109, 117-121.	1.7	52
6	Growth and recrystallization of CeO ₂ thin films deposited on R-plane sapphire by off-axis RF sputtering. Journal of Crystal Growth, 2000, 218, 287-293.	0.7	42
7	Epitaxial growth of high- κ TiO ₂ rutile films on RuO ₂ electrodes. Journal of Vacuum Science & Technology B, 2009, 27, 266-270.	1.3	40
8	Thermally induced voltage shift in capacitance–voltage characteristics and its relation to oxide/semiconductor interface states in Ni/Al ₂ O ₃ /InAlN/GaN heterostructures. Semiconductor Science and Technology, 2009, 24, 035008.	1.0	39
9	Relation between critical current and exponent n in Bi(2223)/Ag tapes. Superconductor Science and Technology, 1997, 10, 605-611.	1.8	38
10	Structure, grain connectivity and pinning of as-deformed commercial MgB ₂ powder in Cu and Fe/Cu sheaths. Superconductor Science and Technology, 2002, 15, 1127-1132.	1.8	37
11	Application of Ru-based gate materials for CMOS technology. Materials Science in Semiconductor Processing, 2004, 7, 271-276.	1.9	35
12	RF Performance of InAlN/GaN HFETs and MOSFETs With f_T up to 21 GHz. IEEE Electron Device Letters, 2010, 31, 180-182.	2.2	34
13	Growth of lanthanum oxide films for application as a gate dielectric in CMOS technology. Materials Science in Semiconductor Processing, 2004, 7, 231-236.	1.9	33
14	Schottky-barrier normally off GaN/InAlN/AlN/GaN HEMT with selectively etched access region. IEEE Electron Device Letters, 2013, 34, 432-434.	2.2	33
15	Injection MOCVD: ferroelectric thin films and functional oxide superlattices. Surface and Coatings Technology, 2000, 133-134, 191-197.	2.2	31
16	Proposal and Performance Analysis of Normally Off n^+ GaN/InAlN/AlN/GaN HEMTs With 1-nm-Thick InAlN Barrier. IEEE Transactions on Electron Devices, 2010, 57, 2144-2154.	1.6	31
17	Adjustment of threshold voltage in AlN/AlGaIn/GaN high-electron mobility transistors by plasma oxidation and Al ₂ O ₃ atomic layer deposition overgrowth. Applied Physics Letters, 2014, 104, .	1.5	31
18	Atomic layer deposition of high-quality Al ₂ O ₃ and Al-doped TiO ₂ thin films from hydrogen-free precursors. Thin Solid Films, 2014, 565, 19-24.	0.8	31

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19	Electrical properties of InAlN/GaN high electron mobility transistor with Al ₂ O ₃ , ZrO ₂ , and GdScO ₃ gate dielectrics. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2011, 29, .	0.6	30
20	Impact of plasma treatment on electrical properties of TiO ₂ /RuO ₂ -based DRAM capacitor. Journal Physics D: Applied Physics, 2013, 46, 385304.	1.3	27
21	Investigation of $\tilde{\sigma}$ -surface donors TM in Al ₂ O ₃ /AlGaIn/GaN metal-oxide-semiconductor heterostructures: Correlation of electrical, structural, and chemical properties. Applied Surface Science, 2017, 426, 656-661.	3.1	27
22	Degradation of LaMnO ₃ $\tilde{\gamma}$ surface layer in LaMnO ₃ $\tilde{\gamma}$ /metal interface. Applied Physics Letters, 2002, 81, 859-861.	1.5	26
23	Interface engineered HfO ₂ -based 3D vertical ReRAM. Journal Physics D: Applied Physics, 2016, 49, 215102.	1.3	26
24	Atomic layer deposition and properties of mixed Ta ₂ O ₅ and ZrO ₂ films. AIP Advances, 2017, 7, .	0.6	26
25	Structure, magnetic and magnetoresistive properties of La _{0.7} Sr _{0.3} Mn _{1-x} Sn _x O ₃ samples (0 $\tilde{\alpha}$ % \tilde{x} $\tilde{\alpha}$ %0.20). Journal of Alloys and Compounds, 2005, 399, 20-26.	2.8	25
26	Precise determination of metal effective work function and fixed oxide charge in MOS capacitors with high- $\tilde{\rho}$ dielectric. Materials Science in Semiconductor Processing, 2006, 9, 969-974.	1.9	24
27	Characterization of rare earth oxides based MOSFET gate stacks prepared by metal-organic chemical vapour deposition. Materials Science in Semiconductor Processing, 2006, 9, 1065-1072.	1.9	24
28	TiO ₂ -based structures for nanoscale memory applications. Materials Science in Semiconductor Processing, 2013, 16, 1186-1195.	1.9	24
29	Self-aligned normally-off metal-oxide-semiconductor n ⁺⁺ GaN/InAlN/GaN high electron mobility transistors. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 1086-1090.	0.8	23
30	Growth of gadolinium oxide films for advanced MOS structure. Microelectronic Engineering, 2005, 80, 154-157.	1.1	22
31	AC magnetization of high T _c superconductors at low superimposed DC magnetic fields. Physica C: Superconductivity and Its Applications, 1989, 160, 1-7.	0.6	21
32	Low-temperature growth of RuO ₂ films for conductive electrode applications. Materials Science in Semiconductor Processing, 2002, 5, 173-177.	1.9	21
33	Electrical properties of TiO ₂ -based MIM capacitors deposited by TiCl ₄ and TTIP based atomic layer deposition processes. Microelectronic Engineering, 2011, 88, 1514-1516.	1.1	21
34	Nanoscale Characterization of TiO ₂ Films Grown by Atomic Layer Deposition on RuO ₂ Electrodes. ACS Applied Materials & Interfaces, 2014, 6, 2486-2492.	4.0	21
35	Low-temperature atomic layer deposition-grown Al ₂ O ₃ gate dielectric for GaN/AlGaIn/GaN MOS HEMTs: Impact of deposition conditions on interface state density. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2017, 35, .	0.6	21
36	Growth of RuO ₂ thin films by liquid injection atomic layer deposition. Thin Solid Films, 2010, 518, 4701-4704.	0.8	20

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37	Resistive switching in TiO ₂ -based metal-insulator-metal structures with Al ₂ O ₃ barrier layer at the metal/dielectric interface. <i>Thin Solid Films</i> , 2014, 563, 10-14.	0.8	20
38	Resistive switching in HfO ₂ -based atomic layer deposition grown metal-insulator-metal structures. <i>Applied Surface Science</i> , 2014, 312, 112-116.	3.1	20
39	Electrically conductive SiC _x (Nb,Ti) _{1-x} ss _{1-x} (Nb,Ti) _{1-x} Css cermet. <i>Journal of the European Ceramic Society</i> , 2006, 26, 1259-1266.	2.8	19
40	<i>Operando</i> diagnostic detection of interfacial oxygen "breathing"™ of resistive random access memory by bulk-sensitive hard X-ray photoelectron spectroscopy. <i>Materials Research Letters</i> , 2019, 7, 117-123.	4.1	19
41	Effect of Ti doping on Ta ₂ O ₅ stacks with Ru and Al gates. <i>Applied Surface Science</i> , 2008, 254, 5879-5885.	3.1	18
42	Influence of oxygen-plasma treatment on AlGaIn/GaN metal-oxide-semiconductor heterostructure field-effect transistors with HfO ₂ by atomic layer deposition: leakage current and density of states reduction. <i>Semiconductor Science and Technology</i> , 2017, 32, 045018.	1.0	18
43	Silicon based MIS photoanode for water oxidation: A comparison of RuO ₂ and Ni Schottky contacts. <i>Applied Surface Science</i> , 2018, 461, 48-53.	3.1	18
44	Growth of SrTiO ₃ thin epitaxial films by aerosol MOCVD. <i>Thin Solid Films</i> , 1995, 260, 187-191.	0.8	17
45	Atomic layer deposition of high-permittivity TiO ₂ dielectrics with low leakage current on RuO ₂ in TiCl ₄ -based processes. <i>Semiconductor Science and Technology</i> , 2012, 27, 074007.	1.0	17
46	Influence of processing and annealing steps on electrical properties of InAlN/GaN high electron mobility transistor with Al ₂ O ₃ gate insulation and passivation. <i>Solid-State Electronics</i> , 2012, 67, 74-78.	0.8	17
47	Atomic layer deposition of rutile-phase TiO ₂ on RuO ₂ from TiCl ₄ and O ₃ : Growth of high-permittivity dielectrics with low leakage current. <i>Journal of Crystal Growth</i> , 2013, 382, 61-66.	0.7	17
48	Epitaxial growth of low-resistivity RuO ₂ films on \bar{c} -oriented Al ₂ O ₃ substrate. <i>Journal of Crystal Growth</i> , 2002, 235, 377-383.	0.7	16
49	High-permittivity metal-insulator-metal capacitors with TiO ₂ rutile dielectric and RuO ₂ bottom electrode. <i>IOP Conference Series: Materials Science and Engineering</i> , 2010, 8, 012024.	0.3	16
50	Optimization and performance of Al ₂ O ₃ /GaIn metal-oxide-semiconductor structures. <i>Microelectronics Reliability</i> , 2007, 47, 790-793.	0.9	15
51	Microstructure-dependent magnetoresistance in La _{1-x} MnO ₃ thin films. <i>Journal of Magnetism and Magnetic Materials</i> , 2000, 211, 67-72.	1.0	14
52	Photoinduced insulator-metal transition in La _{0.81} MnO ₃ /Al ₂ O ₃ /Nb tunnel junctions. <i>Applied Physics Letters</i> , 2001, 78, 1712-1714.	1.5	14
53	Interface States and Trapping Effects in Al ₂ O ₃ - and ZrO ₂ /InAlN/AlN/GaN Metal-Oxide-Semiconductor Heterostructures. <i>Japanese Journal of Applied Physics</i> , 2009, 48, 090201.	0.8	14
54	Atomic layer deposition grown metal-insulator-metal capacitors with RuO ₂ electrodes and Al-doped rutile TiO ₂ dielectric layer. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2011, 29, 01AC09.	0.6	14

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55	Influence of growth temperature on the structure and electrical properties of high- ϵ permittivity TiO_2 films in $\text{TiC}/\text{TiC}_4\text{H}_2/\text{TiC}_3$ atomic layer deposition processes. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2014, 211, 425-432.	0.8	14
56	Magnetism and giant magnetoresistance in $\text{La}_{0.7}\text{Sr}_{0.3}\text{Mn}_1-x\text{MxO}_3$ (M= Cr, Ti) systems. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2004, 1, 1649-1654.	0.8	13
57	Structural and dielectric properties of Ru-based gate/Hf-doped Ta_2O_5 stacks. <i>Applied Surface Science</i> , 2011, 257, 7876-7880.	3.1	13
58	Growth of In - and Ga - Ga_2O_3 epitaxial layers on sapphire substrates using liquid-injection MOCVD. <i>Semiconductor Science and Technology</i> , 2020, 35, 115002.	1.0	13
59	Influence of annealing under oxygen on the chemical and superconducting properties of $\text{YBa}_2\text{Cu}_3\text{O}_x$ single crystals. <i>Journal of the Less Common Metals</i> , 1990, 164-165, 208-214.	0.9	12
60	Superconducting films prepared by aerosol metal organic chemical vapour deposition on substrate with buffer layer. <i>Superconductor Science and Technology</i> , 1997, 10, 657-662.	1.8	12
61	Platinum, Ruthenium and Ruthenium Dioxide Electrodes Deposited by Metal Organic Chemical Vapor Deposition for Oxide Applications. <i>Integrated Ferroelectrics</i> , 2002, 44, 135-142.	0.3	12
62	Thermal stability of GdScO_3 and LaLuO_3 films prepared by liquid injection MOCVD. <i>Vacuum</i> , 2009, 84, 170-173.	1.6	12
63	TiO_2 -Based Metal-Insulator-Metal Structures for Future DRAM Storage Capacitors. <i>ECS Transactions</i> , 2013, 50, 79-87.	0.3	12
64	Development of long Nb and Ge tape with T_c above 20 K. <i>IEEE Transactions on Magnetics</i> , 1981, 17, 2051-2054.	1.2	11
65	Preparation of SrRuO_3 films for advanced CMOS metal gates. <i>Materials Science in Semiconductor Processing</i> , 2004, 7, 265-269.	1.9	11
66	Characterization of interface states in $\text{AlGaIn}/\text{GaIn}$ metal-oxide-semiconductor heterostructure field-effect transistors with HfO_2 gate dielectric grown by atomic layer deposition. <i>Applied Surface Science</i> , 2018, 461, 255-259.	3.1	11
67	Compact Modeling of Complementary Resistive Switching Devices Using Memdiodes. <i>IEEE Transactions on Electron Devices</i> , 2019, 66, 2831-2836.	1.6	11
68	Thin epitaxial CeO_2 films prepared by aerosol MOCVD. <i>Materials Letters</i> , 1994, 21, 377-380.	1.3	10
69	HTS thin films by innovative MOCVD processes. <i>Journal of Alloys and Compounds</i> , 1997, 251, 264-269.	2.8	10
70	Growth of Ru/RuO_2 layers with atomic vapor deposition on plain wafers and into trench structures. <i>Microelectronic Engineering</i> , 2006, 83, 2277-2281.	1.1	10
71	Influence of GaN capping on performance of $\text{InAlIn}/\text{AlIn}/\text{GaN}$ MOS-HEMT with Al_2O_3 gate insulation grown by CVD. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008, 5, 1956-1958.	0.8	10
72	$\text{InAlIn}^*\text{GaN}$ metal-oxide-semiconductor high electron mobility transistor with Al_2O_3 insulating films grown by metal organic chemical vapor deposition using Ar and NH_3 carrier gases. <i>Journal of Vacuum Science & Technology B</i> , 2009, 27, 218.	1.3	10

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73	Ni/Au/Al ₂ O ₃ gate stack prepared by low-temperature ALD and lift-off for MOS HEMTs. Microelectronic Engineering, 2013, 112, 204-207.	1.1	10
74	InGaAs/GaAs metal-oxide-semiconductor heterostructure field-effect transistors with oxygen-plasma oxide and Al ₂ O ₃ double-layer insulator. Applied Physics Letters, 2014, 105, 183504.	1.5	10
75	Annealing, temperature, and bias-induced threshold voltage instabilities in integrated E/D-mode InAlN/GaN MOS HEMTs. Applied Physics Letters, 2017, 111, .	1.5	10
76	MOCVD of YBa ₂ Cu ₃ O _{7-x} thin films using a Ba fluorocarbon-based precursor. Physica C: Superconductivity and Its Applications, 1992, 202, 121-126.	0.6	9
77	Post-deposition processing and oxygen content of TiO ₂ -based capacitors. Microelectronic Engineering, 2011, 88, 1525-1528.	1.1	9
78	Low Equivalent Oxide Thickness TiO ₂ Based Capacitors for DRAM Application. ECS Transactions, 2011, 41, 73-77.	0.3	8
79	Hafnium oxide and tantalum oxide based resistive switching structures for realization of minimum and maximum functions. Journal of Applied Physics, 2018, 124, .	1.1	8
80	Gadolinium Scandate: Next Candidate for Alternative Gate Dielectric in CMOS Technology?. Journal of Electrical Engineering, 2011, 62, 54-56.	0.4	8
81	Chemical vapour deposition of superconducting Nb ₃ Ge controlled by diffusion in the gas phase. Thin Solid Films, 1987, 150, 311-322.	0.8	7
82	Variable temperature insert for a.c. susceptibility measurements at a.c. field amplitudes up to 0.1 T. Cryogenics, 1994, 34, 837-838.	0.9	7
83	Structural and electrical characterization of magnetoresistive La _{0.7} Ca _{0.3} MnO ₃ thin films. Journal of Magnetism and Magnetic Materials, 2003, 262, 150-153.	1.0	7
84	Defects in (La _{0.7} Sr _{0.3} MnO ₃ /SrTiO ₃) ₁₅ superlattices grown by pulsed injection MOCVD. Journal of Crystal Growth, 2003, 259, 358-366.	0.7	7
85	Metal oxide gate electrodes for advanced CMOS technology. Annalen Der Physik, 2004, 13, 31-34.	0.9	7
86	Phase stability of La _{0.5} Sr _{0.5} CoO _{3-y} films upon annealing in hydrogen atmosphere. Journal of Applied Physics, 2006, 100, 044501.	1.1	7
87	Gate oxide thickness dependence of the leakage current mechanism in Ru/Ta ₂ O ₅ /SiON/Si structures. Semiconductor Science and Technology, 2010, 25, 075007.	1.0	7
88	Growth of high crystalline quality thin epitaxial CeO ₂ films on (1102) sapphire. European Physical Journal Special Topics, 1999, 09, Pr8-341-Pr8-347.	0.2	7
89	Si-Based Metal/Insulator/Semiconductor Structures with Ru ₂ (IrO ₂) Films for Photoelectrochemical Water Oxidation. ACS Applied Energy Materials, 2021, 4, 11162-11172.	2.5	7
90	Work function thermal stability of RuO ₂ -rich Ru/SiO ₂ p-channel metal-oxide-semiconductor field-effect transistor gate electrodes. Journal of Applied Physics, 2008, 103, 073702.	1.1	6

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91	Optimization of the ohmic contact processing in InAlN//GaN high electron mobility transistors for lower temperature of annealing. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2010, 7, 108-111.	0.8	6
92	Modeling of the switching I-V characteristics in ultrathin (5 nm) atomic layer deposited HfO ₂ films using the logistic hysteron. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2015, 33, 01A102.	0.6	6
93	Resistive switching in nonplanar HfO ₂ -based structures with variable series resistance. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2015, 33, 01A108.	0.6	6
94	SPICE model for the current-voltage characteristic of resistive switching devices including the snapback effect. <i>Microelectronic Engineering</i> , 2019, 215, 110998.	1.1	6
95	Preparation of YBa ₂ Cu ₃ O ₇ films by low pressure MOCVD using liquid solution sources. <i>European Physical Journal Special Topics</i> , 1993, 03, C3-321-C3-328.	0.2	6
96	Additive Manufacturing in Atomic Layer Processing Mode. <i>Small Methods</i> , 2022, 6, e2101546.	4.6	6
97	Electrical properties and thermal stability of MOCVD grown Ru gate electrodes for advanced CMOS technology. <i>Microelectronic Engineering</i> , 2006, 83, 2412-2416.	1.1	5
98	Evidence of hafnia oxygen vacancy defects in MOCVD grown Hf _x Si _{1-x} O _y ultrathin gate dielectrics gated with Ru electrode. <i>Microelectronic Engineering</i> , 2007, 84, 2366-2369.	1.1	5
99	Preparation of High Permittivity GdScO ₃ Films by Liquid Injection MOCVD. <i>ECS Transactions</i> , 2009, 25, 1061-1064.	0.3	5
100	Analysis of leakage current mechanisms in RuO ₂ /TiO ₂ /RuO ₂ MIM structures. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2011, 29, 01AC08.	0.6	5
101	Atomic Layer Deposition of Thin Oxide Films for Resistive Switching. <i>ECS Transactions</i> , 2013, 58, 163-170.	0.3	5
102	Doping efficiency and electron transport in Al-doped ZnO films grown by atomic layer deposition. <i>Journal of Applied Physics</i> , 2021, 130, 035106.	1.1	5
103	On the relation between T _c measurements and structure inhomogeneity of Nb ₃ Ge superconductor. <i>Acta Physica Academiae Scientiarum Hungaricae</i> , 1982, 53, 419-423.	0.1	4
104	Preparation and characterization of highly densified YBa ₂ Cu ₃ O _{7-δ} Ceramics used for electrochemical oxidation. <i>Zeitschrift Fur Anorganische Und Allgemeine Chemie</i> , 1992, 608, 153-158.	0.6	4
105	Transport critical current in MOCVD YBa ₂ Cu ₃ O ₇ thin films using a pulse technique. <i>Journal of Alloys and Compounds</i> , 1993, 195, 475-478.	2.8	4
106	Title is missing!. <i>Journal of Superconductivity and Novel Magnetism</i> , 2002, 15, 579-582.	0.5	4
107	InAlN/GaN heterostructures for microwave power and beyond. , 2009, , .		4
108	Model for the Current-Voltage Characteristic of Resistive Switches Based on Recursive Hysteretic Operators. <i>IEEE Electron Device Letters</i> , 2015, 36, 944-946.	2.2	4

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109	Effect of deposition temperature on properties of CVD prepared Nb ₃ Ge superconductor. European Physical Journal D, 1989, 39, 196-206.	0.4	3
110	Preparation and properties of Ba-deficient superconducting thin Yâ€“Baâ€“Cuâ€“O films. Journal of Crystal Growth, 1991, 107, 710-711.	0.7	3
111	Characterization of thin superconducting films prepared by metal-organic chemical vapour deposition. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1992, 14, 43-45.	1.7	3
112	TEM characterisation of buffer layers for epitaxial YBa ₂ Cu ₃ O ₇ â€“ growth. Physica Status Solidi A, 1995, 150, 371-380.	1.7	3
113	Growth of YBa ₂ Cu ₃ O ₇ /CeO ₂ /Al ₂ O ₃ heteroepitaxial films by aerosol MOCVD. Journal of Alloys and Compounds, 1997, 251, 284-287.	2.8	3
114	Properties of Al ₂ O ₃ thin films grown by atomic layer deposition. , 2012, , .		3
115	On Passive Permutation Circuits. IEEE Journal on Emerging and Selected Topics in Circuits and Systems, 2015, 5, 173-182.	2.7	3
116	Effect of oxygen concentration and metal electrode on the resistive switching in MIM capacitors with transition metal oxides. Journal of Physics: Conference Series, 2017, 794, 012016.	0.3	3
117	Functionalized graphene transistor for ultrasensitive detection of carbon quantum dots. Journal of Applied Physics, 2019, 126, 214303.	1.1	3
118	Properties of Thin Epitaxial Aerosol MOCVD CeO ₂ Films Grown on (1102) Sapphire. European Physical Journal Special Topics, 1995, 05, C5-533-C5-540.	0.2	3
119	The influence of technology and switching parameters on resistive switching behavior of Pt/HfO ₂ /TiN MIM structures. Facta Universitatis - Series Electronics and Energetics, 2014, 27, 621-630.	0.6	3
120	Critical currents and scaling law in CVD prepared Nb ₃ Ge superconductor alloyed with Al. Cryogenics, 1989, 29, 736-740.	0.9	2
121	Static and dynamic characteristics of Nb ₃ Ge layers for rapid superconducting power switches. Cryogenics, 1991, 31, 590-593.	0.9	2
122	Superconducting properties of YBa ₂ Cu ₃ O ₇ films prepared by aerosol MOCVD. Physica C: Superconductivity and Its Applications, 1994, 235-240, 659-660.	0.6	2
123	On the problem of overlapping XRD scans measured on thin films deposited on monocrystal substrates. Journal of Applied Crystallography, 1999, 32, 736-743.	1.9	2
124	Application of La _{1-x} MnO ₃ giant magnetoresistance sensors for testing of high-TC superconducting tapes. Sensors and Actuators A: Physical, 2001, 91, 21-25.	2.0	2
125	RBS and ERD study of epitaxial RuO ₂ films deposited on different single crystal substrates. Vacuum, 2003, 70, 313-317.	1.6	2
126	Microstructure of HfO ₂ and Hf _x Si _{1-x} O _y Dielectric Films Prepared on Si for Advanced CMOS Application. , 2006, , .		2

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127	Resistive switching in RuO ₂ /TiO ₂ /RuO ₂ MIM structures for non-volatile memory application. , 2010, , .		2
128	Trap-assisted tunnelling current in MIM structures. Open Physics, 2011, 9, .	0.8	2
129	Electrical characterisation of MIS photoanodes annealed under different conditions for solar fuel generation. , 2016, , .		2
130	Performance of HfO _x - and TaO _x -based Resistive Switching Structures for Realization of Minimum and Maximum Functions. MRS Advances, 2018, 3, 3427-3432.	0.5	2
131	Growth of lithium hydride thin films from solutions: Towards solution atomic layer deposition of lithiated films. Beilstein Journal of Nanotechnology, 2019, 10, 1443-1451.	1.5	2
132	Influence of heat treatment on the properties of Bi _{1.8} Pb _{0.2} Sr ₂ Ca ₂ Cu ₃ O _x ceramics and Ag-sheathed tapes. Physica C: Superconductivity and Its Applications, 1994, 235-240, 3441-3442.	0.6	1
133	Growth of magnetoresistant La _{1-x} MnO ₃ films on r-plane cut sapphire. European Physical Journal Special Topics, 2001, 11, Pr3-333-Pr3-339.	0.2	1
134	Layered Si ₃ N ₄ /(SiAlON+TiN) Composites with Self-Diagnostic Ability. , 0, , 559-564.		1
135	Effect of oxygen post-annealing on the magnetoresistance of highly epitaxial La _{0.7} Ca _{0.3} MnO ₃ thin films. Journal of Magnetism and Magnetic Materials, 2004, 272-276, E1501-E1502.	1.0	1
136	Complementarity of X-ray diffraction and RBS in thin film characterization. Vacuum, 2005, 78, 455-461.	1.6	1
137	Thermal Stability of Ru Gate Electrode on HfSiO Dielectric. Materials Research Society Symposia Proceedings, 2006, 917, 1.	0.1	1
138	Current transport in MIM Structures. , 2009, , .		1
139	RuO ₂ /TiO ₂ based MIM capacitors for DRAM application. , 2010, , .		1
140	Distribution of fixed oxide charge in MOS structures with ALD grown Al ₂ O ₃ studied by capacitance measurements. , 2012, , .		1
141	A small Nb ₃ Ge test solenoid. IEEE Transactions on Magnetics, 1987, 23, 577-579.	1.2	0
142	X-ray diffraction analysis of YBCO thin films synthesized by aerosol MOCVD. Physica C: Superconductivity and Its Applications, 1994, 235-240, 657-658.	0.6	0
143	Effect of magnetic field orientation on magnetization of (La _{0.7} Sr _{0.3} MnO ₃ /SrTiO ₃) ₁₅ superlattices. Journal of Magnetism and Magnetic Materials, 2004, 272-276, 1260-1262.	1.0	0
144	Thermal stability of ruthenium MOS gate electrodes. , 0, , .		0

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145	Growth and properties of ruthenium based metal gates for pMOS devices. , 0, , .		0
146	Leakage characteristics of advanced MOS capacitors with hafnium silicate dielectric and Ru electrode. , 2006, , .		0
147	Energy Band Diagram of the Ru/Hf _{0.75} Si _{0.25} O _y /Si Gate Stack. , 2006, , .		0
148	Rapid thermal annealing and performance of Al ₂ O ₃ /GaN metal-oxide-semiconductor structures. , 2006, , .		0
149	InAlN/GaN MOSHEMT with Al ₂ O ₃ insulating film. , 2008, , .		0
150	Electrical characterization of Ru-and RuO ₂ /Ta ₂ O ₅ gate stacks for nanoscale DRAM technology. , 2008, , .		0
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